

**In the Specification:**

Please replace the paragraph beginning at line 13 of page 10 with the following amended paragraph:

Suitable SiC substrates are manufactured by, for example, Cree, Inc., of Durham, N.C., the assignee of the present invention, and the methods for producing are described, for example, U. S. Patent Nos. Re. 34,861; 4,946,547; 5,200,022; and 6,218,680, the contents of which are incorporated herein by reference in their entirety. Similarly, techniques for epitaxial growth of Group III nitrides have been described in, for example, U. S. Patent Nos. 5,210,051; 5,393,993; 5,523,589; and ~~5,292,501~~5,592,501, the contents of which are also incorporated herein by reference in their entirety.